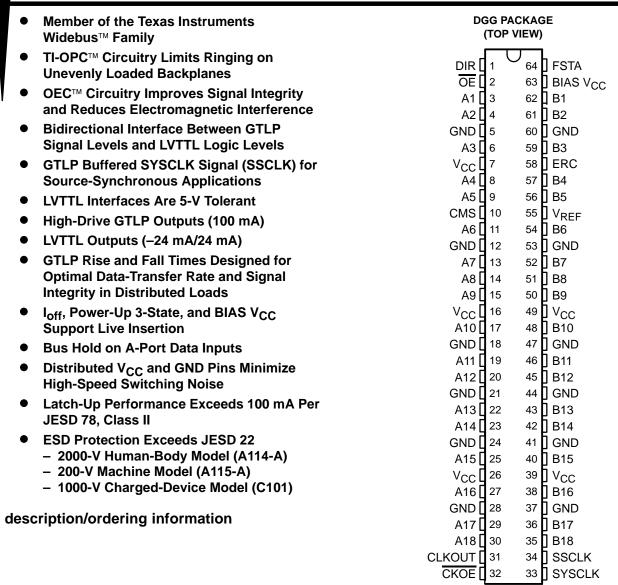
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ORDERING INFORMATION

TA	PACK	AGE [†]	ORDERABLE PART NUMBER	TOP-SIDE MARKING
-40°C to 85°C	TSSOP – DGG	Tape and reel	SN74GTLPH1627DGGR	GTLPH1627

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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description (continued)

The SN74GTLPH1627 is a high-drive, 18-bit bus transceiver that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. The device allows for transparent and latched modes of data transfer. Additionally, with the use of the clock-mode select (CMS) input, the device can be used in source-synchronous and clock-synchronous applications. Source-synchronous applications require the skew between the clock output and data output to be minimized for optimum maximum-frequency system performance. In order to reduce this skew, a flexible setup time adjustment (FSTA) feature is incorporated into the device that sets a predetermined delay between the clock and data. The CMS and direction (DIR) inputs control the mode of the device. The system clock (SYSCLK) and CLKOUT pins are LVTTL compatible, while the source synchronous I/O is GTLP compatible. The benefits include compensation for output-to-output skew coming from the driver itself, and compensation for process skew if more than one driver is used. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard TTL or LVTTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, OEC™ circuitry, and TI-OPC™ circuitry. Improved GTLP OEC and TI-OPC circuits minimize bus-settling time and have been designed and tested using several backplane models. The high drive allows incident-wave switching in heavily loaded backplanes, with equivalent load impedance down to 11 Ω .

GTLP is the Texas Instruments derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification for the SN74GTLPH1627 is given only at the preferred higher noise-margin GTLP, but the user has the flexibility of using this device at either GTL ($V_{TT} = 1.2 \text{ V}$ and $V_{REF} = 0.8 \text{ V}$) or GTLP ($V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$) signal levels. For information on using GTLP devices in FB+/BTL applications, refer to TI application reports, *Texas Instruments GTLP Frequently Asked Questions*, literature number SCEA019, and *GTLP in BTL Applications*, literature number SCEA017.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and are compatible with TTL and 5-V CMOS inputs. V_{REF} is the B-port differential input reference voltage.

This device is fully specified for live-insertion applications using l_{off} , power-up 3-state, and BIAS V_{CC} . The l_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS V_{CC} circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

This GTLP device features TI-OPC circuitry, which actively limits the overshoot caused by improperly terminated backplanes, unevenly distributed cards, or empty slots during low-to-high signal transitions. This improves signal integrity, which allows adequate noise margin to be maintained at higher frequencies.

High-drive GTLP backplane interface devices feature adjustable edge-rate control (ERC). Changing the ERC input voltage between low and high adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

Active bus-hold circuitry holds unused or undriven LVTTL data inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable (\overline{OE}) input should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



functional description

The SN74GTLPH1627 is a high-drive (100 mA), 18-bit bus transceiver containing D-type latches and D-type flip-flops for data-path operation in transparent or latched modes and can replace any of the functions shown in Table 1. Data polarity is noninverting.

Table 1. SN74GTLPH1627 Bus Transceiver Replacement Functions

FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT	18 BIT		
Transceiver	'245, '623, '645	'863	'861	'16245, '16623	'16863		
Buffer/driver	'241, '244, '541		'827	'16241, '16244, '16541	'16825		
Latched transceiver	'543			'16543	'16472		
Latch	'373, '573	'843	'841	'16373	'16843		
SN74GTLPH1627 bus transceiver replaces all above functions.							

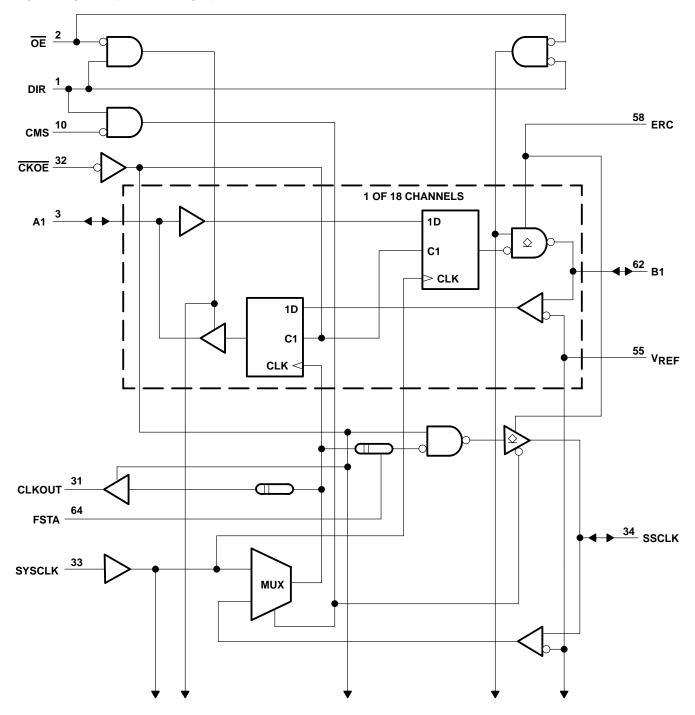
Additionally, the device allows for conversion of the system clock (SYSCLK) to GTLP signal levels (SSCLK) and LVTTL signal levels (CLKOUT). It also provides conversion of a GTLP source-synchronous clock to LVTTL signal levels (CLKOUT).

The device allows for conversion of the LVTTL system clock (SYSCLK) to GTLP (SSCLK) and LVTTL (CLKOUT) signal levels when used as the transmitter and GTLP source-synchronous clock (SSCLK) to LVTTL (CLKOUT) signal levels when used as the receiver in source-synchronous applications. Source-synchronous operation removes time-of-flight restrictions and allows for increased data throughput. CMS is used to switch between system-synchronous mode and clock-synchronous mode. The clock output-enable (CKOE) input is used to switch between latched and transparent mode.

Data flow in each direction is controlled by $\overline{\text{CKOE}}$, clock (SYSCLK or SSCLK), direction (DIR), and $\overline{\text{OE}}$. $\overline{\text{OE}}$ controls the 18 bits of data. The CLKOUT/SSCLK buffered clock path for the A-to-B and B-to-A directions is controlled by $\overline{\text{CKOE}}$. In the data isolation mode ($\overline{\text{OE}}$ high, $\overline{\text{CKOE}}$ low), A data may be stored in one register and/or B data may be stored in the other register.



logic diagram (positive logic)





SN74GTLPH1627 18-BIT LVTTL-TO-GTLP BUS TRANSCEIVER WITH SOURCE SYNCHRONOUS CLOCK OUTPUTS SCES356C – JUNE 2001 – REVISED FERUARY 2003

Function Tables

A-TO-B DIRECTION

INPUTS							OUTPUTS		MODE		
CKOE	OE	CMS	DIR	SYSCLK	Α	SSCLK	CLKOUT	В	MODE		
L	L	Х	L	H or L	Χ	SYSCLK	SYSCLK	B ₀	Latched storage of A		
L	L	Х	L	1	L	SYSCLK	SYSCLK	L	Clocked storage of A	Source synchronous	
L	L	Χ	L	1	Н	SYSCLK	SYSCLK	Н	Clocked Storage of A	Synonicilous	
L	Н	Х	L	Х	Χ	SYSCLK	SYSCLK	Z	Data isolation		
Н	L	Х	L	Х	L	Z	Z	L	Transparent transr	niccion of A	
Н	L	Χ	L	Χ	Н	Z	Z	Н	riansparent transi	HISSIOH OF A	
Н	Н	Х	Х	Х	Χ	Z	Z	Z	Isolation		
L	Н	Н	Х	1	Х	SYSCLK	SYSCLK	Z	Transmit SVSCLV		
L	Н	Н	Χ	H or L	Χ	SYSCLK	SYSCLK	Z	Transmit SYSCLK		

B-TO-A DIRECTION

			INPUT	rs			OUTPUTS					
CKOE	ŌĒ	CMS	DIR	SYSCLK	SSCLK	В	SSCLK	CLKOUT	Α	MODE		
L	L	L	Н	Х	H or L	Χ	Input	SSCLK	A ₀	Latched storage of B	_	
L	L	L	Н	Х	1	L	Input	SSCLK	L	Clasked starage of D	Source synchronous	
L	L	L	Н	Χ	\uparrow	Н	Input	SSCLK	Н	Clocked storage of B	Syncinonous	
L	Н	L	Н	Х	Х	Χ	Input	SSCLK	Z	Data isolation		
L	L	Н	Н	H or L	Output	Χ	SYSCLK	SYSCLK	A ₀	Latched storage of B	<u>.</u>	
L	L	Н	Н	1	Output	L	SYSCLK	SYSCLK	L	Clocked storage of P	Clock synchronous	
L	L	Н	Н	\uparrow	Output	Н	SYSCLK	SYSCLK	Н	Clocked storage of B	Syricinonous	
L	Н	Н	Н	Х	Output	Χ	SYSCLK	SYSCLK	Z	Data isola	tion	
Н	L	Х	Н	Х	Output	L	Z	Z	L	Transparent transp	minoion of D	
Н	L	Χ	Н	Χ	Output	Н	Z	Z	Н	Transparent transr	HISSION OF B	
Н	Н	Х	Х	Х	Output	Χ	Z	Z	Z	Isolation		
L	Н	L	Х	Х	1	Χ	Input	SSCLK	Z	Descript 000HK		
L	Н	L	Χ	Х	H or L	Χ	Input	SSCLK	Z	Receive SS	OLK	

OUTPUT EDGE-RATE CONTROL (ERC)

INPUT ERC LOGIC LEVEL	OUTPUT B-PORT EDGE RATE
Н	Slow
L	Fast



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} and BIAS V _{CC}	0.5 V to 4.6 V
Input voltage range, V _I (see Note 1): A-port and control inputs	-0.5 V to 7 V
B port and V _{REF}	0.5 V to 4.6 V
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1): A port	$-0.5\ V$ to 7 V
B port	\dots –0.5 V to 4.6 V
Current into any output in the low state, I _O : A port	48 mA
B port	200 mA
Current into any A-port output in the high state, I _O (see Note 2)	48 mA
Continuous current through each V _{CC} or GND	±100 mA
Input clamp current, I_{IK} ($V_I < 0$)	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Package thermal impedance, θ _{JA} (see Note 3)	55°C/W
Storage temperature range, T _{stq}	65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
 - 3. The package thermal impedance is calculated in accordance with JESD 51-7.



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recommended operating conditions (see Notes 4 through 7)

			MIN	NOM	MAX	UNIT	
V _{CC} , BIAS V _{CC}	Supply voltage		3.15	3.3	3.45	V	
\/	Tormination voltage	GTL	1.14	1.2	1.26	V	
VTT	Termination voltage	GTLP	1.35	1.5	1.65	V	
V	Reference voltage	GTL	0.74	0.8	0.87	V	
VREF	Reference voltage	GTLP	0.87	1	1.1	V	
V.	Input voltage	B port and SSCLK			V_{TT}	V	
	input voltage	Except B port and SSCLK		Vсс	5.5	V	
V	High-level input voltage	B port and SSCLK	V _{REF} +0.05			V	
VIH	nigh-level input voltage	Except B port and SSCLK	2			V	
V.,	Low-level input voltage	B port and SSCLK			V _{REF} -0.05	V	
VIL	Low-level input voltage	Except B port and SSCLK			0.8	V	
lık	Input clamp current				-18	mA	
loн	High-level output current	A port and CLKOUT			-24	mA	
la.	Low lovel output ourrent	A port and CLKOUT			24	mA	
lor	Low-level output current	B port and SSCLK			100	MA	
Δt/Δν	Input transition rise or fall rate	Outputs enabled			10	ns/V	
Δt/ΔV _{CC}	Power-up ramp rate		20			μs/V	
TA	Operating free-air temperature		-40		85	°C	

NOTES: 4. All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

- 5. Proper connection sequence for use of the B-port I/O precharge feature is GND and BIAS V_{CC} = 3.3 V first, I/O second, and V_{CC} = 3.3 V last, because the BIAS V_{CC} precharge circuitry is disabled when any V_{CC} pin is connected. The control and V_{REF} inputs can be connected anytime, but normally are connected during the I/O stage. If B-port precharge is not required, any connection sequence is acceptable, but generally, GND is connected first.
- 6. V_{TT} and R_{TT} can be adjusted to accommodate backplane impedances if the dc recommended I_{OL} ratings are not exceeded.
- V_{REF} can be adjusted to optimize noise margins, but normally is two-thirds V_{TT}. TI-OPC circuitry is enabled in the A-to-B direction and is activated when V_{TT} > 0.7 V above V_{REF}. If operated in the A-to-B direction, V_{REF} should be set to within 0.6 V of V_{TT} to minimize current drain.



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electrical characteristics over recommended operating free-air temperature range for GTLP (unless otherwise noted)

P/	ARAMETER	TEST CONDITIONS		MIN	TYP [†]	MAX	UNIT	
VIK		V _{CC} = 3.15 V,	I _I = -18 mA			-1.2	V	
		V _{CC} = 3.15 V to 3.45 V,	I _{OH} = -100 μA	V _{CC} -0.2				
Vон	A port and CLKOUT	Vac 245 V	I _{OH} = -12 mA	2.4			V	
	OLKOOT	V _{CC} = 3.15 V	I _{OH} = -24 mA	2				
		V _{CC} = 3.15 V to 3.45 V,	I _{OL} = 100 μA			0.2		
	A port and CLKOUT	V _{CC} = 3.15 V	I _{OL} = 12 mA			0.4		
		vCC = 3.15 v	I _{OL} = 24 mA			0.5		
VOL		V _{CC} = 3.15 V to 3.45 V,	I _{OL} = 100 μA			0.2	V	
	B name and CCCLK		I _{OL} = 10 mA			0.2		
	B port and SSCLK	V _{CC} = 3.15 V	I _{OL} = 64 mA			0.4		
			I _{OL} = 100 mA			0.55		
lį	SYSCLK and control inputs	V _{CC} = 3.45 V,	V _I = 0 to 5.5 V			±10	μΑ	
loz [‡]	B port and SSCLK	$V_{CC} = 3.45 \text{ V}, V_{REF} \text{ within } 0.6 \text{ V of } V_{TT},$	V _O = 0 to 2.3 V			±10		
lOZ+	CLKOUT	V _{CC} = 3.45 V,	V _O = 0 to 5.5 V			±10	μΑ	
I _{OZH} ‡	A port	V _{CC} = 3.45 V,	VO = VCC		:	10	μΑ	
l _{OZL} ‡	A port	V _{CC} = 3.45 V,	V _O = GND			-10	μΑ	
I _{BHL} §	A port	V _{CC} = 3.15 V,	V _I = 0.8 V	75			μΑ	
I _{BHH} ¶	A port	V _{CC} = 3.15 V,	V _I = 2 V	- 75			μΑ	
I _{BHLO} #	A port	$V_{CC} = 3.45 \text{ V},$	$V_I = 0$ to V_{CC}	500			μΑ	
Івнно	A port	V _{CC} = 3.45 V,	$V_I = 0$ to V_{CC}	-500			μΑ	
		$V_{CC} = 3.45 \text{ V}, I_{O} = 0,$	Outputs high			±10 10 -10 -50 50		
Icc	A port, B port, or SSCLK	V_I (A-port or control input) = V_{CC} or GND,	Outputs low			50	mA	
	JOGOLK	V _I (B port) = V _{TT} or GND	Outputs disabled			50		
∆lcc≉		V_{CC} = 3.45 V, One A-port or control input at Other A-port or control inputs at V_{CC} or GN				1.5	mA	
0.	SYSCLK inputs	V _I = 3.15 V or 0			4	5		
Ci	Control inputs	V _I = 3.15 V or 0			3.5	5.5	pF	
C.	A port	V _O = 3.15 V or 0			7.5	9.5	pF	
C _{io}	B port or SSCLK	V _O = 1.5 V or 0			9.5	12		
Со	CLKOUT	V _O = 3.15 V or 0			6	7.5	pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



For I/O ports, the parameter I_I includes the off-state output leakage current.

[§] The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL}max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to V_{IL}max.

[¶] The bus-hold circuit can source at least the minimum high sustaining current at V_{IH}min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH}min.

[#]An external driver must source at least I_{BHLO} to switch this node from low to high.

An external driver must sink at least IBHHO to switch this node from high to low.

^{*}This is the increase in supply current for each input that is at the specified TTL voltage level, rather than V_{CC} or GND.

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hot-insertion specifications for A port over recommended operating free-air temperature range

PARAMETER		TEST CONDITION	NS .	MIN	MAX	UNIT
l _{off}	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_{I} or $V_{O} = 0$ to 5.5 V		10	μΑ
lozpu	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 V \text{ to } 3 V,$	OE = 0		±30	μΑ
IOZPD	$V_{CC} = 1.5 \text{ V to } 0,$	$V_0 = 0.5 \text{ V to 3 V},$	OE = 0		±30	μΑ

live-insertion specifications for B port over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS		MIN	MAX	UNIT
loff	$V_{CC} = 0$,	BIAS $V_{CC} = 0$,	V_I or $V_O = 0$ to 1.5 V		10	μΑ
lozpu	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	BIAS $V_{CC} = 0$,	$V_0 = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ
IOZPD	$V_{CC} = 1.5 \text{ V to } 0,$	BIAS $V_{CC} = 0$,	$V_0 = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ
Inc (PIAS Vac)	V _{CC} = 0 to 3.15 V	BIAS V _{CC} = 3.15 V to 3.45 V,	V _O (B port) = 0 to 1.5 V		5	mA
ICC (BIAS VCC)	V _{CC} = 3.15 V to 3.45 V	DIAS VCC = 3.15 V to 3.45 V,	VO (Β port) = 0 to 1.5 V	10 ±30 ±30	μΑ	
VO	$V_{CC} = 0$,	BIAS $V_{CC} = 3.3 \text{ V}$,	IO = 0	0.95	1.05	V
IO	$V_{CC} = 0$,	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	V _O (B port) = 0.6 V	-1	·	μΑ

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (unless otherwise noted)

			MIN	MAX	UNIT
f _{clock}	Clock frequency			175	MHz
		SYSCLK (A to B) or (B to A) high or low	2.5		
		SYSCLK to CLKOUT high or low	2.8		
		SYSCLK to SSCLK (FSTA GND) high or low	2.8		
t_{W}	Pulse duration	SYSCLK to SSCLK (FSTA V _{CC}) high or low	2.3		ns
		SSCLK (B to A) high or low	2.8		
		SSCLK to CLKOUT high or low	2.8		
		CKOE (A to B) or (B to A) high	2.5	.5 .8 .8 .8 .8 .8 .5 .1 .2 .6 .4 .8 .3 .7 .1 0	
		A before SYSCLK↑	1.1		
		B before SYSCLK↑	2.2		
t _{su}	Setup time	B before SSCLK↑	1.6		ns
		A before CKOE↓	1.4		
		B before CKOE↓	0.8	175 2.5 2.8 2.8 2.8 2.8 2.8 2.8 2.8 2.8 2.5 1.1 2.2 1.6 1.4 0.8 0.3 0.7 1.1	
		A after SYSCLK↑	0.3		
		B after SYSCLK↑	0.7		
th	Hold time	B after SSCLK↑	1.1		ns
		A after CKOE↓	0		
		B after CKOE↓	0.7		

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switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 1)

PARAMETER	СГОСК	FROM (INPUT)	TO (OUTPUT)	EDGE RATET	FSTA	MIN	түр‡	MAX	UNIT	
		A or B	B or A	-	_	175				
	CVCCLK	SYSCLK	CLKOUT	-	_	175				
	SYSCLK	SYSCLK	SSCLK	-	GND	175			MHz	
fmax		SYSCLK	SSCLK	-	VCC	150			IVIHZ	
l	SSCLK	В	А	-	-	175				
	SSCLK	SSCLK	CLKOUT	-	-	175				
	ı	A	В	Fast	-	2.3		6.2		
l I	ı] ^	Ь	Slow	-	3		7.3		
l [-	CKOE	В	Fast	-	2.6		6	ns	
^t pd	ı	CKOE	Ь	Slow	_	3.1		7.6	115	
	ı	SYSCLK	В	Fast	_	2.6		6	6 7.1	
	1	STOCER	В	Slow	_	3		7.1		
t _{en}		OE B Fast	OE B	ь	East		2.3		5.1	ns
	ı		_	2.7		5.5	115			
t _{en}	_	OF	OE B	Slow	_	2.9		6	ns	
^t dis	_	OE .	В	Slow	_	3.6		6.6		
	_	Rise time, B and SSCLK outputs		Fast		1.1			ns	
t _r	_	(20% to	(20% to 80%)		_	2.1			113	
t _f		Fall time, B and		Fast	Fast _		1.8			
ነ		(80% to	0 20%)	Slow	_		2.4		ns	
	ı	В	Α	_	-	1.5		4.6		
	_	CKOE	Α	_	_	2.1		6		
l [-	SYSCLK	А	-	_	1.9		6		
^t pd	-	SSCLK	А	-	-	2.3		6.6	ns	
	-	SYSCLK	CLKOUT	-	-	3.3		8.3		
i		SSCLK	CLKOUT	-	-	3.7		9		
t _{en}		05				1.6		5		
^t dis	_	ŌE	Α	_	_	2.1		6.4	ns	
t _{en}		CKOE	CLKOLIT	ĺ		2		5.2		
^t dis	_	CRUE	CLKOUT	_	_	2.4		6.1	ns	

[†] Slow (ERC = H) and Fast (ERC = L)

[‡] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

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skew characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{REF} = 1 V (unless otherwise noted); standard lumped loads, C_L = 30 pF for B port (see Figure 1)[†]

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE‡	FSTA	TEST CONDITIONS	MIN	MAX	UNIT
t _{sk(LH)} §	SYSCLK	В	Fast	-			0.5	ns
t _{sk(HL)} §	OTOOLIK						0.5	113
t _{sk(LH)} §	SYSCLK	В	Slow	_			0.5	ns
t _{sk(HL)} §			0.0				0.5	
t _{sk(LH)} §	SYSCLK	SSCLK + ΔB (see Figure 2)	Fast	GND	V _{CC} = 3.15 V, T = 85°C	3.2	4.6	ns
					V _{CC} = 3.3 V, T = 25°C	2.9	4.3	
					$V_{CC} = 3.45 \text{ V}, T = -40^{\circ}\text{C}$	2.8	4.1	
^t sk(HL) [§]	SYSCLK	SSCLK + ΔB (see Figure 2)	Fast	GND	V _{CC} = 3.15 V, T = 85°C	3.6	5	ns
					$V_{CC} = 3.3 \text{ V, T} = 25^{\circ}\text{C}$	3.4	4.8	
					$V_{CC} = 3.45 \text{ V}, T = -40^{\circ}\text{C}$	3.3	4.6	
_	SYSCLK	SSCLK + ∆B (see Figure 2)	Slow	GND	V _{CC} = 3.15 V, T = 85°C	3	4.6	ns
t _{sk(LH)} §					$V_{CC} = 3.3 \text{ V, T} = 25^{\circ}\text{C}$	2.6	4.3	
					$V_{CC} = 3.45 \text{ V, T} = -40^{\circ}\text{C}$	2.4	4	
	SYSCLK	SSCLK + ∆B (see Figure 2)	Slow	GND	$V_{CC} = 3.15 \text{ V}, T = 85^{\circ}\text{C}$	3.7	5.2	ns
t _{sk(HL)} §					V _{CC} = 3.3 V, T = 25°C	3.6	5.1	
					$V_{CC} = 3.45 \text{ V, T} = -40^{\circ}\text{C}$	3.5	5	
	SYSCLK	SSCLK + ∆B (see Figure 2)	Fast	VCC	V _{CC} = 3.15 V, T = 85°C	6.5	8.3	ns
t _{sk(LH)} §					V _{CC} = 3.3 V, T = 25°C	6.3	8.2	
					V _{CC} = 3.45 V, T = -40°C	5.6	7.4	
t _{sk(HL)} §	SYSCLK	SSCLK + ΔB (see Figure 2)	Fast	Vcc	V _{CC} = 3.15 V, T = 85°C	7	8.7	ns
					V _{CC} = 3.3 V, T = 25°C	6.5	8.3	
					V _{CC} = 3.45 V, T = -40°C	6.2	8	
^t sk(LH) [§]	SYSCLK	SSCLK + ΔB (see Figure 2)	Slow	Vcc	V _{CC} = 3.15 V, T = 85°C	6.4	8.3	ns
					V _{CC} = 3.3 V, T = 25°C	5.9	7.7	
					V _{CC} = 3.45 V, T = -40°C	5.5	7.4	
t _{sk(HL)} §	SYSCLK	SSCLK + ΔB (see Figure 2)	Slow	Vcc	V _{CC} = 3.15 V, T = 85°C	7.2	8.9	
					V _{CC} = 3.3 V, T = 25°C	6.8	8.6	ns
					V _{CC} = 3.45 V, T = -40°C	6.6	8.3	
t _{sk(t)} §	SYSCLK	В	Fast	_			1.4	
			Slow	_			2	ns
^t sk(prLH) [¶]	0)(00) 1(В					1.8	
t _{sk(prHL)} ¶	SYSCLK			_		2.8		ns

[†] Actual skew values between the GTLP outputs could vary on the backplane due to the loading and impedance seen by the device.

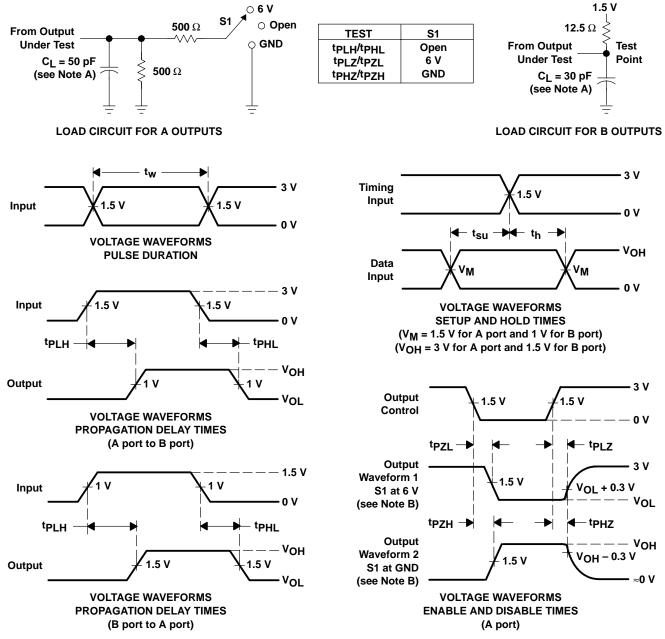


[‡] Slow (ERC = H) and Fast (ERC = L)

[§] t_{sk(LH)}/t_{sk(HL)} and t_{sk(t)} – Output-to-output skew is defined as the absolute value of the difference between the actual propagation delay for all outputs with the same packaged device. The specifications are given for specific worst-case V_{CC} and temperature. The specifications apply to any outputs switching in the same direction, either high to low [t_{sk(HL)}], low to high [t_{sk(LH)}] or in opposite directions, both low to high and high to low [t_{sk(t)}].

¹ tsk(prLH) or tsk(prHL) – Part-to-part skew is designed as the absolute value of the difference between the actual propagation delay for all outputs from device to device. The parameter is specified for a specific worst-case VCC and temperature. Furthermore, these values are provided by SPICE simulations.

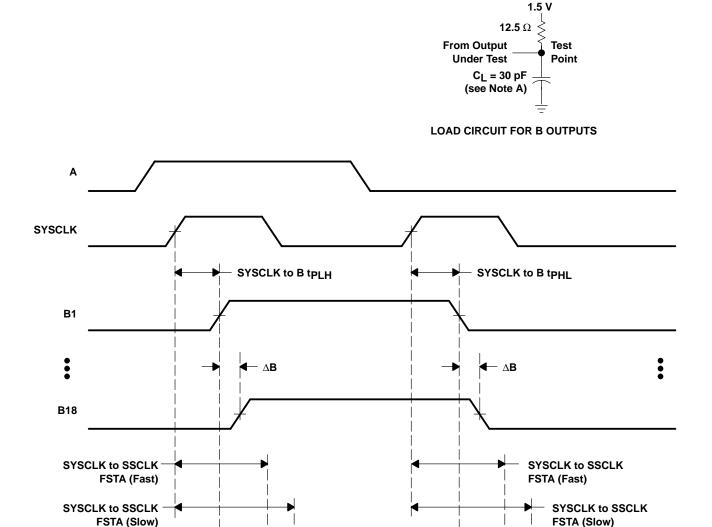
PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. Load circuit for A outputs also is used for CLKOUT; load circuit for B outputs also is used for SSCLK.

Figure 1. Load Circuits and Voltage Waveforms





NOTES: A. C_L includes probe and jig capacitance.

tsk(LH) FSTA (Fast)

tsk(LH) FSTA (Slow)

SSCLK

B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns.

^tsk(HL) FSTA (Fast)

tsk(HL) FSTA (Slow)

- C. The outputs are measured one at a time with one transition per measurement.
- D. Load circuit for B outputs also is used for SSCLK.

Figure 2. Load Circuit and SYSCLK to SSCLK + ΔB Skew Waveforms



DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application is probably a distributed load. The physical representation is shown in Figure 3. This backplane, or distributed load, can be closely approximated to a resistor inductance capacitance (RLC) circuit, as shown in Figure 4. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer to better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

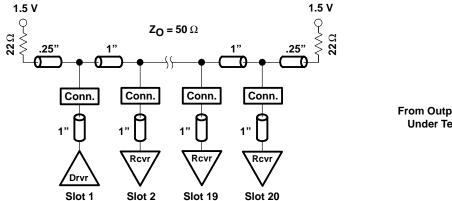


Figure 3. High-Drive Test Backplane

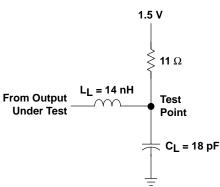


Figure 4. High-Drive RLC Network

switching characteristics over recommended operating conditions for the bus transceiver function (unless otherwise noted) (see Figure 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE†	FSTA	түр‡	UNIT
^t PLH	A	В	Fast	_	4.8	ns
^t PHL					4.2	
^t PLH			Slow	_	5.6	
^t PHL					5.2	
^t PLH	SYSCLK	В	Fast	-	4.9	ns
^t PHL					4.5	
^t PLH			Slow	ı	5.5	
^t PHL					5.2	
t _r	Rise time, B and	SSCLK outputs	Fast	-	0.9	ns
	(20% to	o 80%)	Slow	_	1.3	
+.	Fall time, B and	SSCLK outputs	Fast	_	2.3	ns
^t f	(80% to	o 20%)	Slow	_	2.7	

[†] Slow (ERC = H) and Fast (ERC = L)

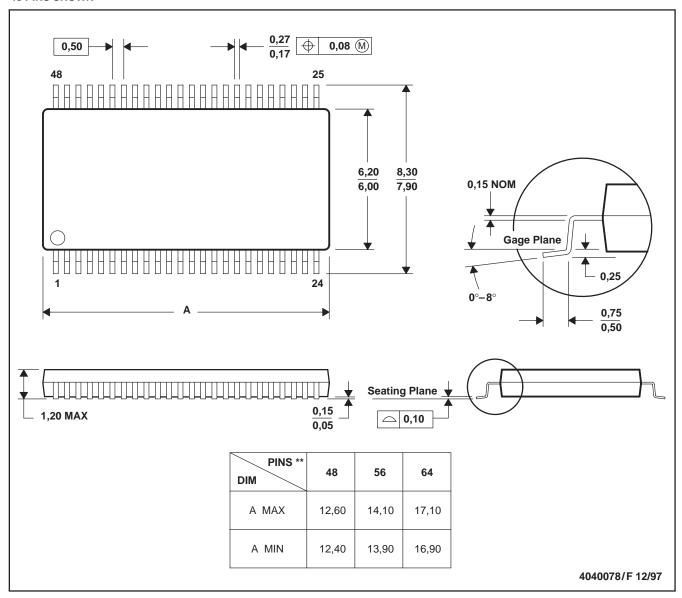


[‡] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. All values are derived from TI-SPICE models.

DGG (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

48 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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